

Transducer

Process of converting one form of energy into another is called transduction, and device that performs this function called transducer.

The devices which converts other from of electrical energy into electrical from are transducer.

Advantage

- Very small Power Inv.
- Effects of friction are minimized
- output easily measured, stored, processed.

based of electrical circuit parameter

Classification of transducers

- Resistance → Capacitance → Inductance → Voltage or current

↳ of a resistor element

$$\hookrightarrow R = \frac{\rho L}{A}$$

Strain ϵ

freq

Strain Gauge.

Resistance strain gauges are also known as piezo resistive gauges.

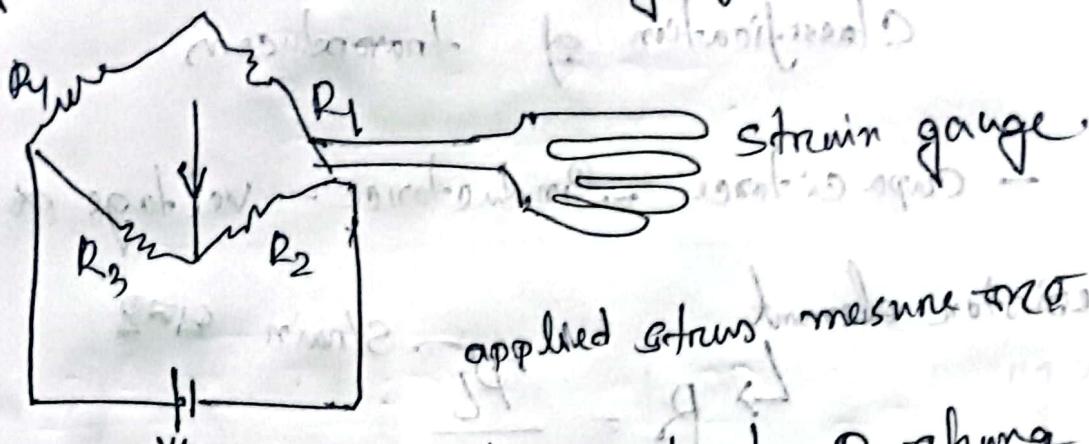
• unit of strain is micro strain.

$$\hookrightarrow 1 \text{ Micro strain} = 1 \mu\text{m/m}$$

Piezo electric effect: It is the change in electric polarization of the material when there is the application of mechanical pressure.

Strain \Rightarrow Change in Resistance

Bridge circuit of strain gauge.



resistance

$$R = \frac{\rho L}{A - \text{area}}$$

applied strain

- Resistivity ρ changing

such dimension \Rightarrow of Gauge

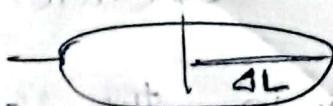
Perzo positive effect

Strain Gauge factor = $Gf = 1 + 2f$

Theory of strain Gauge;



$$R = \frac{\rho L}{A} \quad \text{for } \Delta R = \frac{\rho \Delta L}{A}$$



Strain = $\frac{\Delta L}{L}$ out for reading

$$\text{Strain} = \frac{\text{Change in dimension}}{\text{original dimension}}$$

C2 $A_1 L$ & $A_2 L$ strain \Rightarrow

$$C = \frac{\Delta A}{A} \quad \text{where } \Delta L = C \cdot L$$

- Force $\frac{PL}{A}$ (i) \rightarrow longitudinal strain $\frac{\Delta L}{L}$
- Area " " " lateral strain $\frac{\Delta A}{A}$

transverse differential.

$$R = \frac{PL}{A}$$

$$\frac{dP}{ds} = \frac{d}{ds} \left(\frac{PL}{A} \right)$$

$$\frac{dP}{ds} = \frac{P}{A} \left(\frac{\partial L}{\partial s} \right) - \frac{PL}{A^2} \frac{\partial A}{\partial s} + \frac{L}{A} \frac{\partial P}{\partial s}$$

$$\frac{1}{R} \frac{dR}{ds} = \frac{P}{AR} \frac{dL}{ds} - \frac{PL}{A^2 R} \frac{dA}{ds}$$

$$\frac{1}{R} \frac{dR}{ds} = \frac{P}{A \cdot \frac{PL}{A}} \frac{dL}{ds} - \frac{PL}{A^2 \cdot \frac{PL}{A}} \frac{dA}{ds} + \frac{L}{A \cdot \frac{PL}{A}} \frac{dP}{ds}$$

$$\therefore \frac{1}{R} \cdot \frac{dR}{ds} = \frac{L}{A} \cdot \frac{dL}{ds} - \frac{1}{A} \frac{dA}{ds} + \frac{1}{P} \cdot \frac{dP}{ds} \quad \text{--- (ii)}$$

we know $A = \pi r^2$ write $R = \frac{D}{2}$

$$\pi \left(\frac{D}{2}\right)^2 = \frac{\pi D^2}{4}$$

A @ differential.

$$\frac{dA}{ds} = \frac{\pi}{4} \cdot D^2 = \frac{\pi}{4} 2D \frac{dD}{ds} - \textcircled{i}$$

① मान (ii) को दर्शाएँ $\left(\frac{dA}{ds}\right)$ का

$$\frac{dP}{Ds} = \frac{1}{L} \frac{dL}{ds} - \frac{1}{2D} \times \frac{\pi}{4} \cdot 2D \frac{dD}{ds} + \frac{1}{P} \frac{dP}{ds}$$

$$= \frac{1}{L} \frac{dL}{ds} - \frac{2}{D} \frac{dD}{ds} + \frac{1}{P} \frac{dP}{ds} \quad \text{--- (iii)}$$

Poisson's Ratio = $\frac{\text{Lateral Strain}}{\text{Longitudinal Strain}}$

Lateral Strain

Longitudinal Strain

$$\frac{\partial A}{A} / \frac{\partial D}{D}$$

D Pressure

A Area

D dimension

mm

$$\frac{ab}{cb}$$

$$(ii) \quad \therefore \frac{ab}{2D} = -V \frac{\partial L}{\partial L} - \textcircled{iv}$$

Q) $\frac{dR}{R}$ (iii) $\frac{dL}{L}$

$$\frac{1}{R} \cdot \frac{dR}{ds} = \frac{1}{L} \frac{dL}{ds} + \frac{2v}{L} \frac{\partial L}{\partial s} + \frac{1}{P} \frac{\partial P}{\partial s} - v$$

$$\frac{1}{R} \frac{dR}{ds} = \frac{1}{L} \frac{dL}{ds} [1 + 2v] + \frac{1}{P} \frac{\partial P}{\partial s} \quad \text{--- (i)}$$

Gauge factor: output change with respect to input.

$$G_f = \frac{\frac{dR}{R}}{\frac{dL}{L}} \quad \left\{ \begin{array}{l} \text{change in resistance} \\ \text{change in length} \end{array} \right\} \text{ are } G_f.$$

$$\therefore \frac{\Delta R}{R} = G_f \cdot \frac{\Delta L}{L}$$

For small change Δs due to stress ($\Delta R \propto \Delta R$ forever)

Ans

$$\frac{\Delta R}{R} = \frac{\Delta L}{L} + 2v \frac{\Delta L}{L} + \frac{\Delta P}{P}$$

$$\frac{\Delta R}{R} = \frac{\Delta L/L}{\Delta L/L} + 2v \frac{\Delta L/L}{\Delta L/L} + \frac{\Delta P/P}{\Delta L/L} \quad \left[\frac{\Delta L}{L} \text{ is } \frac{\Delta s}{s} \right]$$

$$G_y = 1 + 2\nu + \frac{\Delta P/P}{\Delta L/L}$$

$$= 1 + 2\nu + \frac{\Delta P/P}{E}$$

(ii)

$$\begin{aligned} G_y &= \\ E &= \text{strain} \\ &= \frac{\Delta L/L}{P} \end{aligned}$$

$$\Rightarrow G_y \div \boxed{1 + 2\nu}$$

proved

effect negligible

small, ΔL
negligible

small, ΔL

ΔL small

ΔL small

$$\frac{\Delta L}{L} = \frac{\Delta P}{P}$$

$$\frac{\Delta L}{L} = \frac{\Delta P}{P}$$

$(1 + 2\nu) \approx 1$ so $\Delta P/P \approx \Delta L/L$

$$\frac{QD}{q} + \frac{QD}{S} \nu = \frac{QD}{E} + \frac{QD}{S}$$

Application of PV / Solar cell.

- A solar cell also known as PV cell.
- It is an electrical device that converts light energy into electrical energy through the photovoltaic effect.
- Solar cell is P-N junction diode.
- Solar cell produce current voltage 0.5 - 0.6 Volts.
- Individual solar cells can be combined to form modules commonly known as solar panels.

working principle of solar cell.

- When light reaches the P-N junction, light photons can easily enter the junction through n-type layer.
- The light energy, in the form of photons, supplies sufficient energy to the junction to create number of electron-hole pairs.

- The free electron on the depletion can quickly come to n-type side.
- The holes in the depletion can quickly come to the P-type side.
- In processing - Photo-voltage set up.

If we connect a small load across the junction, there will be tiny current flowing.

Materials used in Solar cell.

Silicon • GaAs • CdTe • CuInSe₂

Advantage Solar cell

- No pollution associated.
- It must for a long time.
- No maintenance cost.

Disadvantage Solar cell.

- High cost installation.
- Low efficiency.
- Cloudy day to don't work.

Application of optoelectronic

Transducer

- Opto electronics \Rightarrow It deals with application of electronics in lightwave: devices that interact with light;
- optical electronic
light semi-conductor. [means this device detect light and transfer light signal to electrical signals] \downarrow \leftarrow $\text{Light transducers.}$

Types of optoelectronics

- photodiode • solar cells • Light Emitting Diodes • optical fiber
- laser diode.

Photo diode: Convert light energy to electrical energy.

- contain active P-N junction, operated reverse bias.
- when a proton with plenty of energy strikes in semiconductor, an hole pair is created.

- This electric field across the depletion zone is equal to a negative voltage.
- This method called Omnire photoelectric effect.
- It can be used in 3 modes: photovoltaic as
- a solar cell, forward biased as an LED, reverse biased as a photo detector.
- photo diodes used [Cameras, medical, communication devices]

Photo diode \ominus forward bias G connect then Ammeter - Only current G change detect work since of C.R. reverse bias we get.

Solar Cell • A solar cell or photovoltaic cell is an electronic device that directly converts sunlight into electricity.

Light Emitting diodes: It is a diode. works on forward bias condition

Forward bias voltage applied to an LED



when a voltage is applied to the leads of the LED the electrons combine with the holes within device release energy from photons.

optical fiber: It is a plastic and made from glass.

- Sometimes it's thin than human hair.
- It includes 3 layers \rightarrow a core, a cladding and a jacket.
- \downarrow protective layer.
- \downarrow different colors.
- \downarrow right transmitting region

- orange Clr cable \Rightarrow single mode fiber.
- yellow n v \Rightarrow multi-mode fiber.

Laser Diodes

A laser diodes Q.I convert electrical energy

into light energy Line infrared diodes LEDs

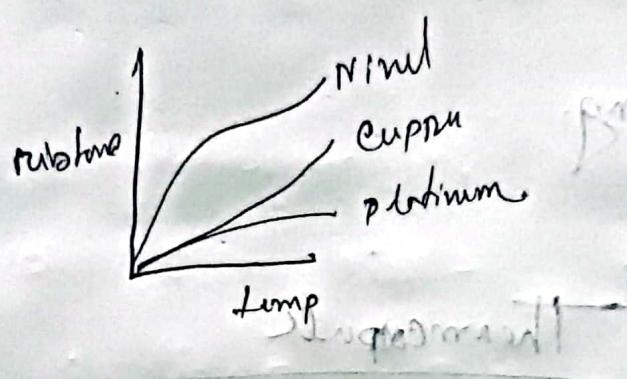
LED principle / Application

- LED based Automatic emergency light
- Mains operated LED light
- Display of Dailed telephone on 7 Seg Display
- Solar powered Led light Auto Intensity control



Resistance temp detector (RTD)

RTD works on the principle that the electric resistance of a metal changes due to change in its temp.



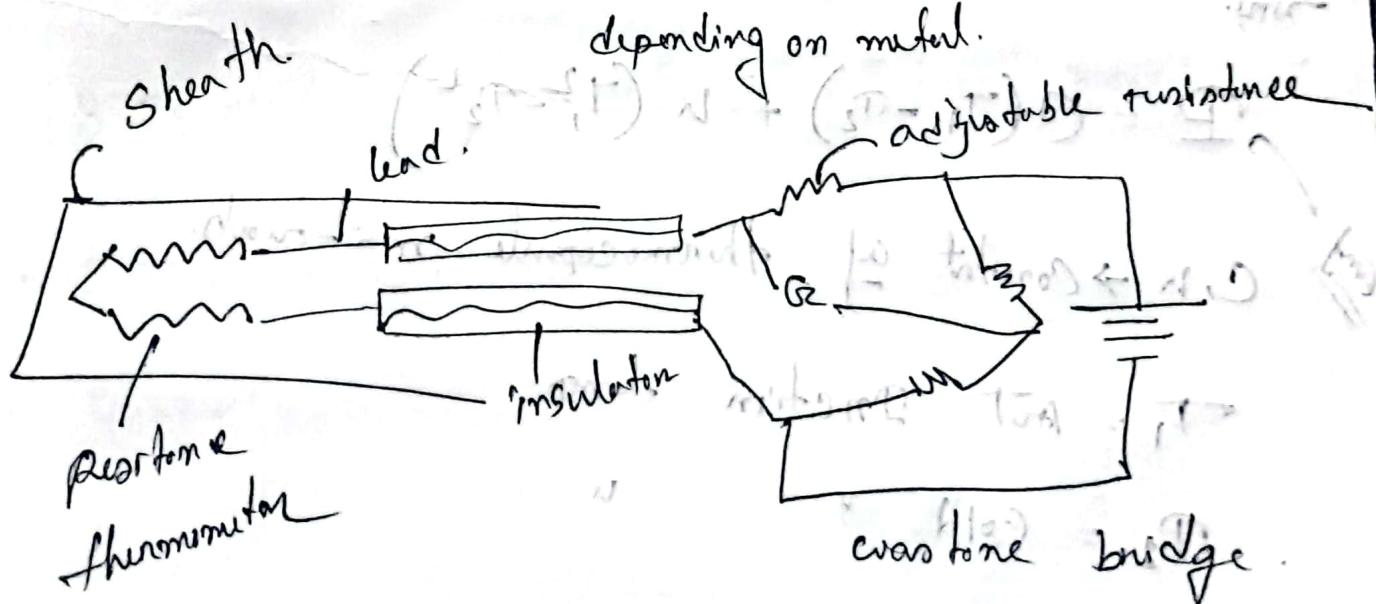
The co-relationship of RTD is

$$R(T) = R_0 \left[1 + A(T - T_0) + B(T - T_0)^2 \right]$$

depending on metal.

resistance of Temp

resistance term



Construction of RTD

Application RTD

- Food Processing
- Textile, plastic Industry.
- Petrochemical.
- Air conditioning.

Thermocouple

To go a sensor we to measure the temp
 $E = C(T_1 - T_2) + \alpha(T_1^2 - T_2^2)$

Voltage difference θ_{1234} or 2θ , θ voltmeter (new)

$$E = C(T_1 - T_2) + \alpha(T_1^2 - T_2^2)$$

$C, \alpha \rightarrow$ Constant of thermocouple materials.

$T_1 =$ hot junction temp

$T_2 =$ cold junction

RTD is mentioned

Math's

During experiments with copper constants thermo-couple Q1 was found that $C = 3.75 \times 10^{-2} \text{ mv/}^{\circ}\text{C}$ and $\kappa = 4.5 \times 10^{-5} \text{ MV/}^{\circ}\text{C}$. If $T_1 = 100^{\circ}\text{C}$ and the cold junction T_2 is kept in ice.

Compute $E_{\text{m.v.}}$.

Ans

We know

$$E = C(T_1 - T_2) + \kappa(T_1^L - T_2^L)$$

$$= 3.75 \times 10^{-2} \frac{\text{mv}}{\text{C}} (100 - 0^{\circ}\text{C})$$

$$+ 4.5 \times 10^{-5} \frac{\text{mv}}{\text{C}} ((100)^2 - (0)^2)$$

$$= (3.75 \times 10^{-2} \times 100) \text{ mv} + (4.5 \times 10^{-5} \times 100^2) \text{ mv}$$

$$= 3.75 \text{ mv} + 0.45 \text{ mv}$$

$$\approx 4.10 \text{ MV.}$$

Given values

$$C = 3.75 \times 10^{-2} \text{ MV/}^{\circ}\text{C}$$

$$\kappa = 4.5 \times 10^{-5} \text{ MV/}^{\circ}\text{C}$$

$$T_1 = 100^{\circ}\text{C}$$

$$T_2 = 0^{\circ}\text{C}$$

Difference

RTD

Thermocouple

- | | |
|--|---|
| <ul style="list-style-type: none">• It is more suited to measure the lower temp range.• The measuring range is -200°C to 500°C.• Good stability.• good accuracy• More expensive than thermocouple.• O/P change in Resistance. | <ul style="list-style-type: none">• It is suited to measure the larger temp range.• The measuring range is -180°C to 2320°C.• Poor stability.• poor Accuracy.• Cheaper than RTD.• O/P change in voltage. |
|--|---|